MC100EL58DR2G Datasheet

DiGi Electronics Part Number	MC100EL58DR2G-DG
Manufacturer	onsemi
Manufacturer Product Number	MC100EL58DR2G
Description	IC MULTIPLEXER 1 X 2:1 8SOIC
Detailed Description	Multiplexer 1 x 2:1 8-SOIC

https://www.DiGi-Electronics.com

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

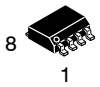
Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
MC100EL58DR2G	onsemi
Series:	Product Status:
100EL	Active
Type:	Circuit:
Multiplexer	1 x 2:1
Independent Circuits:	Current - Output High, Low:
1	-
Voltage Supply Source:	Voltage - Supply:
Dual Supply	±4.2V ~ 5.7V
Operating Temperature:	Mounting Type:
-40°C ~ 85°C	Surface Mount
Package / Case:	Supplier Device Package:
8-SOIC (0.154", 3.90mm Width)	8-SOIC
Base Product Number:	
100EL58	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8542.39.0001	

5.0 V ECL 2:1 Multiplexer
MC10EL58, MC100EL58



SOIC−8 NB
D SUFFIX
CASE 751−07

TSSOP−8
DT SUFFIX
CASE 948R−02

Description

The MC10EL/100EL58 is a 2:1 multiplexer. The device is functionally equivalent to the E158 device with higher performance capabilities. With propagation delays and output transition times significantly faster than the E158, the EL58 is ideally suited for those applications which require the ultimate in AC performance.

The 100 Series contains temperature compensation.

Features

- 230 ps Propagation Delay
- PECL Mode Operating Range:
  - V_{CC} = 4.2 V to 5.7 V with V_{EE} = 0 V
- NECL Mode Operating Range:
  - V_{CC} = 0 V with V_{EE} = −4.2 V to −5.7 V
- Internal Input Pulldown Resistors on D_a, D_b, and SEL
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

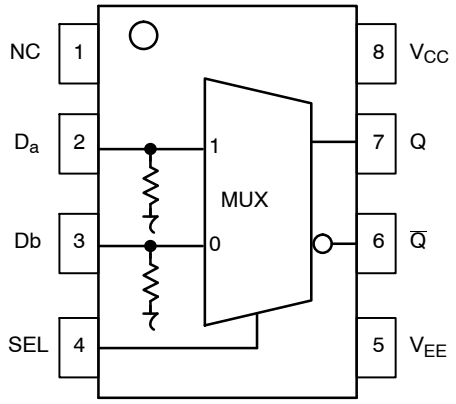
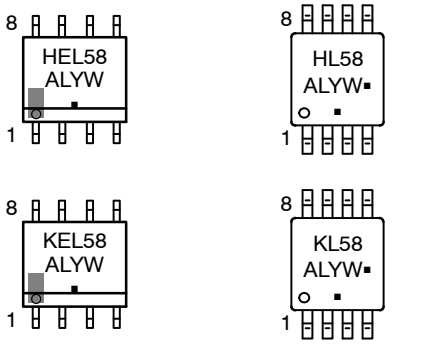


Figure 1. Logic Diagram and Pin Assignment

MARKING DIAGRAM



H = MC10
K = MC100
4Z = MC10
2O = MC100
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
$\overline{M}$ = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

NOTE: Some of the device on this data sheet have been **DISCONTINUED**. Please refer to the table on page 6

Table 1. PIN DESCRIPTION

PIN	FUNCTION
D_a, Db	ECL Data Inputs
Q, $\overline{Q}$	ECL Data Outputs
SEL	ECL Select Input
V_{CC}	Positive Supply
V_{EE}	Negative Supply
NC	No Connect

Table 2. FUNCTION TABLE

SEL*	Data
H	a
L	b

* Pin will default low when left open.

Table 3. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	75 kΩ
Internal Input Pullup Resistor	N/A
ESD Protection Human Body Model Machine Model	 > 1 kV > 100 V
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1) SOIC−8 TSSOP−8	 Level 1 Level 3
Flammability Rating Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in
Transistor Count	45
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	

1. Refer to Application Note AND8003/D for additional information.

Table 4. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V_{CC}	PECL Mode Power Supply	V_{EE} = 0 V		8	V
V_{EE}	NECL Mode Power Supply	V_{CC} = 0 V		−8	V
V_I	PECL Mode Input Voltage NECL Mode Input Voltage	V_{EE} = 0 V V_{CC} = 0 V	$V_I \le V_{CC}$ $V_I \ge V_{EE}$	6 −6	V
I_{out}	Output Current	Continuous Surge		50 100	mA
T_A	Operating Temperature Range			−40 to +85	°C
T_{stg}	Storage Temperature Range			−65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC−8 NB	190 130	°C/W
θ_{JC}	Thermal Resistance (Junction-to-Case)		SOIC−8 NB	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP−8	185 140	°C/W
T_{sol}	Wave Solder (Pb-Free)	<2 to 3 sec @ 260°C		265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. JEDEC standard multilayer board − 2S2P (2 signal, 2 power)

Table 5. 10EL SERIES PECL DC CHARACTERISTICS (V_{CC}= 5.0 V; V_{EE}= 0.0 V (Note 1))

		−40°C			25°C			85°C			
Symbol	Characteristic	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Unit
I_{EE}	Power Supply Current		14	17		14	17		14	17	mA
V_{OH}	Output HIGH Voltage (Note 2)	3920	4010	4110	4020	4105	4190	4090	4185	4280	mV
V_{OL}	Output LOW Voltage (Note 2)	3050	3200	3350	3050	3210	3370	3050	3227	3405	mV
V_{IH}	Input HIGH Voltage	3770		4110	3870		4190	3940		4280	mV
V_{IL}	Input LOW Voltage	3050		3500	3050		3520	3050		3555	mV
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.3			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.
1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.06 V / −0.5 V.
2. Outputs are terminated through a 50 ohm resistor to V_{CC}−2 volts.

Table 6. 10EL SERIES NECL DC CHARACTERISTICS (V_{CC}= 0.0 V; V_{EE}= −5.0 V (Note 1))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current		14	17		14	17		14	17	mA
V_{OH}	Output HIGH Voltage (Note 2)	−1080	−990	−890	−980	−895	−810	−910	−815	−720	mV
V_{OL}	Output LOW Voltage (Note 2)	−1950	−1800	−1650	−1950	−1790	−1630	−1950	−1773	−1595	mV
V_{IH}	Input HIGH Voltage	−1230		−890	−1130		−810	−1060		−720	mV
V_{IL}	Input LOW Voltage	−1950		−1500	−1950		−1480	−1950		−1445	mV
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.3			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.06 V / −0.5 V.
2. Outputs are terminated through a 50 ohm resistor to V_{CC}−2 volts.

Table 7. 100EL SERIES PECL DC CHARACTERISTICS (V_{CC}= 5.0 V; V_{EE}= 0.0 V (Note 1))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current		14	17		14	17		16	19	mA
V_{OH}	Output HIGH Voltage (Note 2)	3915	3995	4120	3975	4045	4120	3975	4050	4120	mV
V_{OL}	Output LOW Voltage (Note 2)	3170	3305	3445	3190	3295	3380	3190	3295	3380	mV
V_{IH}	Input HIGH Voltage	3835		4120	3835		4120	3835		4120	mV
V_{IL}	Input LOW Voltage	3190		3525	3190		3525	3190		3525	mV
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.8 V / −0.5 V.
2. Outputs are terminated through a 50 ohm resistor to V_{CC}−2 volts.

Table 8. 100EL SERIES NECL DC CHARACTERISTICS (V_{CC}= 0.0 V; V_{EE}= −5.0 V (Note 1))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
I_{EE}	Power Supply Current		14	17		14	17		16	19	mA
V_{OH}	Output HIGH Voltage (Note 2)	−1085	−1005	−880	−1025	−955	−880	−1025	−955	−880	mV
V_{OL}	Output LOW Voltage (Note 2)	−1830	−1695	−1555	−1810	−1705	−1620	−1810	−1705	−1620	mV
V_{IH}	Input HIGH Voltage	−1165		−880	−1165		−880	−1165		−880	mV
V_{IL}	Input LOW Voltage	−1810		−1475	−1810		−1475	−1810		−1475	mV
I_{IH}	Input HIGH Current			150			150			150	μA
I_{IL}	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. Input and output parameters vary 1:1 with V_{CC}. V_{EE} can vary +0.8 V / −0.5 V.
2. Outputs are terminated through a 50 ohm resistor to V_{CC}−2 volts.

Table 9. AC CHARACTERISTICS (V_{CC}= 5.0 V; V_{EE}= 0.0 V or V_{CC}= 0.0 V; V_{EE}= −5.0 V (Note 1))

Symbol	Characteristic	−40°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
fmax	Maximum Toggle Frequency					1.5					GHz
t_{PLH} t_{PHL}	Propagation Delay to Output D to Q SEL to Q	 60 90	 220 250	 380 410	 120 150	 230 260	 340 370	 140 170	 250 280	 360 390	ps
t_{JITTER}	Random Clock Jitter (RMS)					0.9					ps
t_r t_f	Output Rise/Fall Times Q (20% − 80%)	100	225	350	100	225	350	100	225	350	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

1. 10 Series: V_{EE} can vary +0.06 V / −0.5 V.
   100 Series: V_{EE} can vary +0.8 V / −0.5 V.

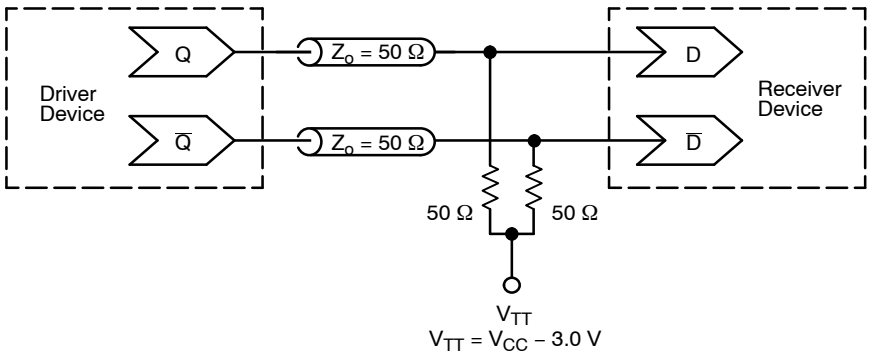


Figure 2. Typical Termination for Output Driver and Device Evaluation (See Application Note AND8020/D − Termination of ECL Logic Devices.)

ORDERING INFORMATION

Device	Package	Shipping†
MC10EL58DR2G	SOIC−8 (Pb-Free)	2500 / Tape & Reel
MC10EL58DTG	TSSOP−8 (Pb-Free)	100 Units / Rail
MC100EL58DTG	TSSOP−8 (Pb-Free)	100 Units / Rail

DISCONTINUED (Note 2)

Device	Package	Shipping†
MC10EL58DG	SOIC−8 (Pb-Free)	98 Units / Rail
MC100EL58DG	SOIC−8 (Pb-Free)	98 Units / Rail
MC100EL58DR2G	SOIC−8 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

2. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

Resource Reference of Application Notes

AN1405/D – ECL Clock Distribution Techniques

AN1406/D – Designing with PECL (ECL at +5.0 V)

AN1503/D – ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D – Metastability and the ECLinPS Family

AN1568/D – Interfacing Between LVDS and ECL

AN1672/D – The ECL Translator Guide

AND8001/D – Odd Number Counters Design

AND8002/D – Marking and Date Codes

AND8020/D – Termination of ECL Logic Devices

AND8066/D – Interfacing with ECLinPS

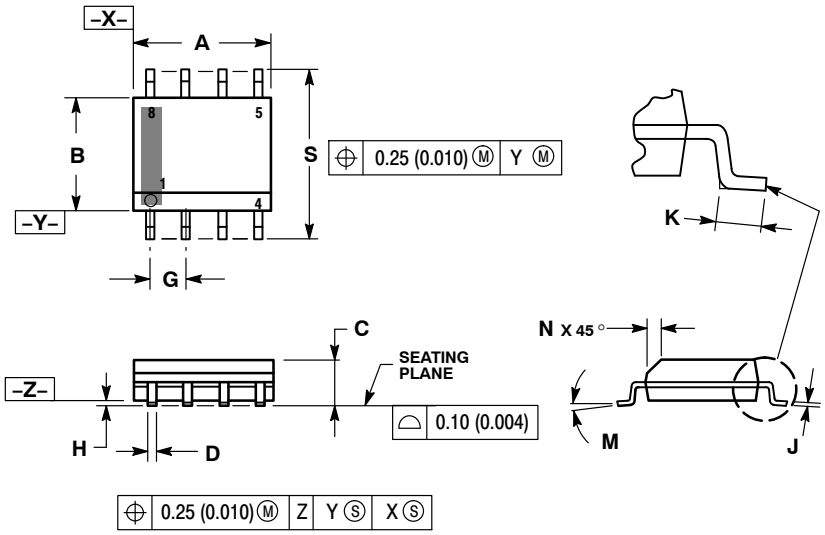
AND8090/D – AC Characteristics of ECL Devices

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

SCALE 1:1

SOIC−8 NB
CASE 751−07
ISSUE AK

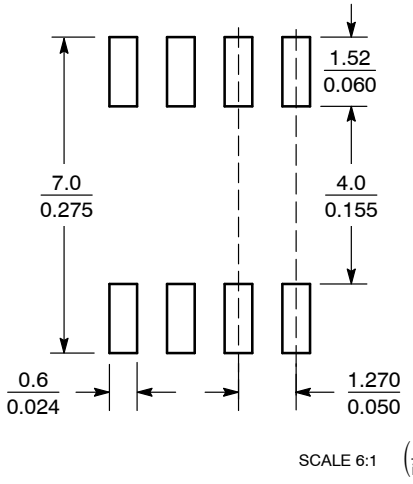
DATE 16 FEB 2011



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751−01 THRU 751−06 ARE OBSOLETE. NEW STANDARD IS 751−07.

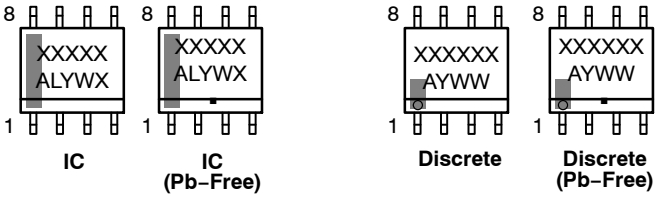
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42564B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	**SOIC−8 NB**		**PAGE 1 OF 2**

SOIC−8 NB
CASE 751−07
ISSUE AK

DATE 16 FEB 2011

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. COLLECTOR
4. EMITTER
5. EMITTER
6. BASE
7. BASE
8. EMITTER

STYLE 2:
PIN 1. COLLECTOR, DIE, #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. BASE, #2
6. EMITTER, #2
7. BASE, #1
8. EMITTER, #1

STYLE 3:
PIN 1. DRAIN, DIE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. GATE, #2
6. SOURCE, #2
7. GATE, #1
8. SOURCE, #1

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
7. ANODE
8. COMMON CATHODE

STYLE 5:
PIN 1. DRAIN
2. DRAIN
3. DRAIN
4. DRAIN
5. GATE
6. GATE
7. SOURCE
8. SOURCE

STYLE 6:
PIN 1. SOURCE
2. DRAIN
3. DRAIN
4. SOURCE
5. SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 7:
PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

STYLE 8:
PIN 1. COLLECTOR, DIE #1
2. BASE, #1
3. BASE, #2
4. COLLECTOR, #2
5. COLLECTOR, #2
6. EMITTER, #2
7. EMITTER, #1
8. COLLECTOR, #1

STYLE 9:
PIN 1. EMITTER, COMMON
2. COLLECTOR, DIE #1
3. COLLECTOR, DIE #2
4. EMITTER, COMMON
5. EMITTER, COMMON
6. BASE, DIE #2
7. BASE, DIE #1
8. EMITTER, COMMON

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT
4. GROUND
5. GROUND
6. BIAS 2
7. INPUT
8. GROUND

STYLE 11:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 12:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 14:
PIN 1. N−SOURCE
2. N−GATE
3. P−SOURCE
4. P−GATE
5. P−DRAIN
6. P−DRAIN
7. N−DRAIN
8. N−DRAIN

STYLE 15:
PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

STYLE 16:
PIN 1. EMITTER, DIE #1
2. BASE, DIE #1
3. EMITTER, DIE #2
4. BASE, DIE #2
5. COLLECTOR, DIE #2
6. COLLECTOR, DIE #2
7. COLLECTOR, DIE #1
8. COLLECTOR, DIE #1

STYLE 17:
PIN 1. VCC
2. V2OUT
3. V1OUT
4. TXE
5. RXE
6. VEE
7. GND
8. ACC

STYLE 18:
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 19:
PIN 1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

STYLE 20:
PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3
4. CATHODE 4
5. CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 22:
PIN 1. I/O LINE 1
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 23:
PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 24:
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

STYLE 25:
PIN 1. VIN
2. N/C
3. REXT
4. GND
5. IOUT
6. IOUT
7. IOUT
8. IOUT

STYLE 26:
PIN 1. GND
2. dv/dt
3. ENABLE
4. ILIMIT
5. SOURCE
6. SOURCE
7. SOURCE
8. VCC

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 28:
PIN 1. SW_TO_GND
2. DASIC_OFF
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBULK
7. VBULK
8. VIN

STYLE 29:
PIN 1. BASE, DIE #1
2. EMITTER, #1
3. BASE, #2
4. EMITTER, #2
5. COLLECTOR, #2
6. COLLECTOR, #2
7. COLLECTOR, #1
8. COLLECTOR, #1

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
3. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
6. SOURCE 1/DRAIN 2
7. SOURCE 1/DRAIN 2
8. GATE 1

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ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
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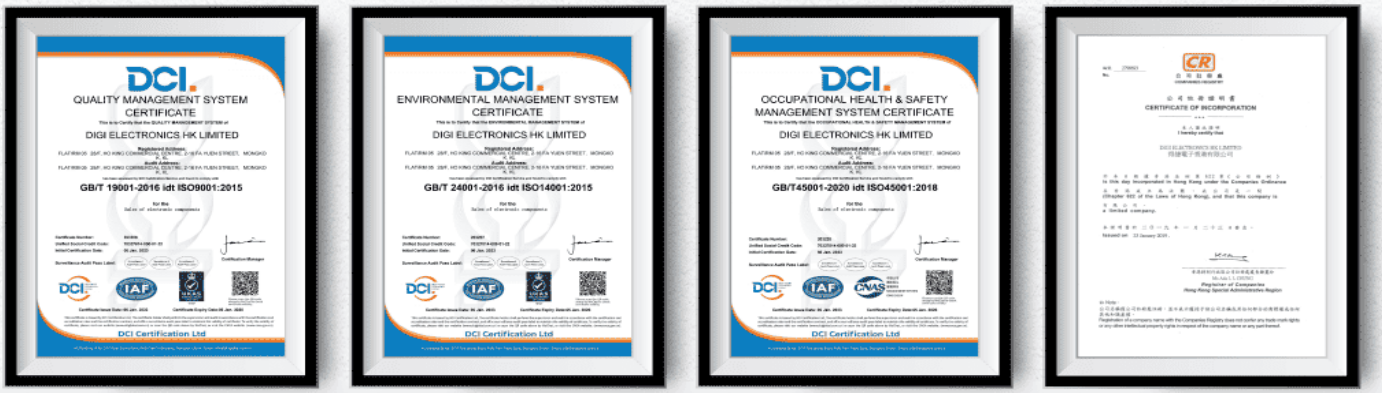

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